

# Susanne Stemmer

## List of Publications by Year in descending order

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312  
papers

15,448  
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19608

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314  
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314  
docs citations

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times ranked

13835  
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced Gas Sensing by Individual SnO <sub>2</sub> Nanowires and Nanobelts Functionalized with Pd Catalyst Particles. Nano Letters, 2005, 5, 667-673.	4.5	1,319
2	Thermal Conductivity Reduction and Thermoelectric Figure of Merit Increase by Embedding Nanoparticles in Crystalline Semiconductors. Physical Review Letters, 2006, 96, 045901.	2.9	756
3	Comparison of methods to quantify interface trap densities at dielectric/III-V semiconductor interfaces. Journal of Applied Physics, 2010, 108, .	1.1	352
4	Quantitative Atomic Resolution Scanning Transmission Electron Microscopy. Physical Review Letters, 2008, 100, 206101.	2.9	342
5	Epitaxial SrTiO <sub>3</sub> films with electron mobilities exceeding 30,000 cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> . Nature Materials, 2010, 9, 482-484.	13.3	342
6	Magnetism in polycrystalline cobalt-substituted zinc oxide. Physical Review B, 2003, 68, .	1.1	304
7	Emergence of room-temperature ferroelectricity at reduced dimensions. Science, 2015, 349, 1314-1317.	6.0	259
8	Experimental quantification of annular dark-field images in scanning transmission electron microscopy. Ultramicroscopy, 2008, 108, 1653-1658.	0.8	225
9	Electrostatic carrier doping of GdTiO <sub>3</sub> /SrTiO <sub>3</sub> interfaces. Applied Physics Letters, 2011, 99, .	1.5	214
10	Standardless Atom Counting in Scanning Transmission Electron Microscopy. Nano Letters, 2010, 10, 4405-4408.	4.5	212
11	Low-dimensional Mott material: Transport in ultrathin epitaxial LaNiO <sub>3</sub> films. Applied Physics Letters, 2010, 96, .	1.5	189
12	Position averaged convergent beam electron diffraction: Theory and applications. Ultramicroscopy, 2010, 110, 118-125.	0.8	184
13	Engineering chemically abrupt high-k metal oxide-silicon interfaces using an oxygen-gettering metal overlayer. Journal of Applied Physics, 2004, 96, 3467-3472.	1.1	182
14	High-mobility BaSnO <sub>3</sub> grown by oxide molecular beam epitaxy. APL Materials, 2016, 4, .	2.2	181
15	Low-loss, tunable bismuth zinc niobate films deposited by rf magnetron sputtering. Applied Physics Letters, 2003, 83, 2411-2413.	1.5	177
16	Resistive switching and its suppression in Pt/Nb:SrTiO <sub>3</sub> junctions. Nature Communications, 2014, 5, 3990.	5.8	167
17	Growth of high-quality SrTiO <sub>3</sub> films using a hybrid molecular beam epitaxy approach. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 461-464.	0.9	155
18	Two-Dimensional Electron Gases at Complex Oxide Interfaces. Annual Review of Materials Research, 2014, 44, 151-171.	4.3	154



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37	Impact of stress on oxygen vacancy ordering in epitaxial (La <sub>0.5</sub> Sr <sub>0.5</sub> )CoO <sub>3</sub> thin films. Applied Physics Letters, 2003, 82, 3427-3429.	1.5	88
38	Temperature dependence of the dielectric tunability of pyrochlore bismuth zinc niobate thin films. Applied Physics Letters, 2005, 86, 032901.	1.5	88
39	Suppression of subcutaneous oxidation during the deposition of amorphous lanthanum aluminate on silicon. Applied Physics Letters, 2004, 84, 4629-4631.	1.5	87
40	Three-Dimensional Imaging of Individual Dopant Atoms in $\text{SrTiO}_3$ . Physical Review Letters, 2013, 111, 266101.	2.9	86
41	Structure and stability of La <sub>2</sub> O <sub>3</sub> /SiO <sub>2</sub> layers on Si(001). Applied Physics Letters, 2001, 79, 102-104.	1.5	85
42	La-doped SrTiO <sub>3</sub> films with large cryogenic thermoelectric power factors. Applied Physics Letters, 2013, 102, .	1.5	83
43	Atomically abrupt and unpinned Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As interfaces: Experiment and simulation. Journal of Applied Physics, 2009, 106, .	1.1	81
44	Low surface roughness and threading dislocation density Ge growth on Si (001). Journal of Crystal Growth, 2008, 310, 4273-4279.	0.7	79
45	Two-dimensional electron gas in $\text{SrTiO}_3$ -doped $\text{SrTiO}_3$ . Physical Review B, 2010, 82, .	1.1	78
46	Enhancing the electron mobility of SrTiO <sub>3</sub> with strain. Applied Physics Letters, 2011, 98, .	1.5	77
47	Growth defects in GaN films on 6H-SiC substrates. Applied Physics Letters, 1996, 68, 2678-2680.	1.5	75
48	Reducing Thermal Conductivity of Crystalline Solids at High Temperature Using Embedded Nanostructures. Nano Letters, 2008, 8, 2097-2099.	4.5	75
49	Nitrogen-passivated dielectric/InGaAs interfaces with sub-nm equivalent oxide thickness and low interface trap densities. Applied Physics Letters, 2013, 102, .	1.5	73
50	A quantitative approach for spatially-resolved electron energy-loss spectroscopy of grain boundaries and planar defects on a subnanometer scale. Ultramicroscopy, 1995, 59, 215-227.	0.8	71
51	Grain boundary segregation in high-purity, yttria-stabilized tetragonal zirconia polycrystals (Y-TZP). Journal of the European Ceramic Society, 1998, 18, 1565-1570.	2.8	71
52	Application of Metastable Phase Diagrams to Silicate Thin Films for Alternative Gate Dielectrics. Japanese Journal of Applied Physics, 2003, 42, 3593-3597.	0.8	71
53	Microwave dielectric properties of tunable capacitors employing bismuth zinc niobate thin films. Journal of Applied Physics, 2005, 97, 084110.	1.1	70
54	Lanthanum silicate gate dielectric stacks with subnanometer equivalent oxide thickness utilizing an interfacial silica consumption reaction. Journal of Applied Physics, 2005, 98, 024314.	1.1	69

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55	Carrier-Controlled Ferromagnetism in $\text{SrTiO}_3$ . Physical Review X, 2012, 2, .	2.8	69
56	Film/Substrate Orientation Relationship in the $\text{AlN}/6\text{H-SiC}$ Epitaxial System. Physical Review Letters, 1996, 77, 1797-1800.	2.9	68
57	Molecular beam epitaxy of $\text{Cd}_3\text{As}_2$ on a III-V substrate. APL Materials, 2016, 4, .	2.2	68
58	Negative magnetoresistance due to conductivity fluctuations in films of the topological semimetal $\text{Cd}_3\text{As}_2$ . Physical Review B, 2016, 93, 040407.	1.1	68
59	Dislocations in $\text{PbTiO}_3$ Thin Films. Physica Status Solidi A, 1995, 147, 135-154.	1.7	66
60	Toward an artificial Mott insulator: Correlations in confined high-density electron liquids in $\text{SrTiO}_3$ . Physical Review B, 2012, 86, .	1.1	64
61	Structural origins of the properties of rare earth nickelate superlattices. Physical Review B, 2013, 87, .	1.1	64
62	Analysis of trap state densities at $\text{HfO}_2/\text{In}_0.53\text{Ga}_{0.47}\text{As}$ interfaces. Applied Physics Letters, 2010, 96, .	1.5	63
63	Thin Dielectric Film Thickness Determination by Advanced Transmission Electron Microscopy. Microscopy and Microanalysis, 2003, 9, 493-508.	0.2	61
64	Fixed charge in high- $k$ /GaN metal-oxide-semiconductor capacitor structures. Applied Physics Letters, 2012, 101, 102905.	1.5	61
65	Transport in ferromagnetic $\text{GdTiO}_3/\text{SrTiO}_3$ heterostructures. Applied Physics Letters, 2011, 98, .	1.5	60
66	Conductivity enhancement of ultrathin $\text{LaNiO}_3$ films in superlattices. Applied Physics Letters, 2010, 97, .	1.5	59
67	A heterojunction modulation-doped Mott transistor. Journal of Applied Physics, 2011, 110, .	1.1	59
68	Nanoscale quantification of octahedral tilts in perovskite films. Applied Physics Letters, 2012, 100, .	1.5	59
69	Thermal conductivity as a metric for the crystalline quality of $\text{SrTiO}_3$ epitaxial layers. Applied Physics Letters, 2011, 98, 221904.	1.5	58
70	Element Specific Monolayer Depth Profiling. Advanced Materials, 2014, 26, 6554-6559.	11.1	58
71	Correlation between stoichiometry, strain, and metal-insulator transitions of $\text{NdNiO}_3$ films. Applied Physics Letters, 2015, 106, .	1.5	58
72	Conduction-band edge and Shubnikov-de Haas effect in low-electron-density $\text{SrTiO}_3$ . Physical Review B, 2013, 88, .	1.1	57

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73	Interface-induced magnetism in perovskite quantum wells. Physical Review B, 2013, 88, .	1.1	56
74	Characterization of oxygen-deficient SrCoO <sub>3-δ</sub> by electron energy-loss spectroscopy and Z-contrast imaging. Solid State Ionics, 2000, 130, 71-80.	1.3	55
75	Influence of strain on the dielectric relaxation of pyrochlore bismuth zinc niobate thin films. Applied Physics Letters, 2004, 84, 957-959.	1.5	55
76	Quantitative comparisons of contrast in experimental and simulated bright-field scanning transmission electron microscopy images. Physical Review B, 2009, 80, .	1.1	55
77	Thickness dependence of the quantum Hall effect in films of the three-dimensional Dirac semimetal Cd <sub>3</sub> As <sub>2</sub> . APL Materials, 2018, 6, .	2.2	55
78	Optical conductivity of $\text{LaNiO}_3$ . Coherent transport and correlation driven mass enhancement. Physical Review B, 2010, 82, .	2.3	54
79	Evidence of a topological Hall effect in Eu <sup>2+</sup> /Sm <sup>3+</sup> /TiO <sub>3</sub> . Applied Physics Letters, 2017, 111, .	1.5	52
80	Epitaxial Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> thin films synthesized by metal-organic chemical vapor deposition. Applied Physics Letters, 2000, 76, 3106-3108.	1.5	51
81	The Interface between Single Crystalline (001) LaAlO <sub>3</sub> and (001) Silicon. Japanese Journal of Applied Physics, 2005, 44, L617-L619.	0.8	51
82	Symmetry Lowering in Extreme-Electron-Density Perovskite Quantum Wells. Physical Review Letters, 2013, 110, 256401.	2.9	51
83	Limitations to the room temperature mobility of two- and three-dimensional electron liquids in SrTiO <sub>3</sub> . Applied Physics Letters, 2015, 106, .	1.5	51
84	Interface atomic structure of epitaxial ErAs layers on (001) In <sub>0.53</sub> Ga <sub>0.47</sub> As and GaAs. Applied Physics Letters, 2005, 86, 241901.	1.5	50
85	Frequency dispersion in III-V metal-oxide-semiconductor capacitors. Applied Physics Letters, 2012, 100, .	1.5	49
86	Growth window and effect of substrate symmetry in hybrid molecular beam epitaxy of a Mott insulating rare earth titanate. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	0.9	48
87	Quantum critical behaviour in confined SrTiO <sub>3</sub> quantum wells embedded in antiferromagnetic SmTiO <sub>3</sub> . Nature Communications, 2014, 5, 4258.	5.8	48
88	0.5 V Supply Voltage Operation of In <sub>0.65</sub> Ga <sub>0.35</sub> As/Ga <sub>0.4</sub> Sb <sub>0.6</sub> Tunnel FET. IEEE Electron Device Letters, 2015, 36, 20-22.	2.2	48
89	Stability of ZrO <sub>2</sub> layers on Si (001) during high-temperature anneals under reduced oxygen partial pressures. Journal of Applied Physics, 2002, 92, 82-86.	1.1	46
90	Phase Separation in Hafnium Silicates for Alternative Gate Dielectrics. Journal of the Electrochemical Society, 2003, 150, F173.	1.3	46

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91	Electrical and material characterizations of high-permittivity Hf <sub>x</sub> Ti <sub>1-x</sub> O <sub>2</sub> gate insulators. Journal of Applied Physics, 2005, 98, 054506.	1.1	46
92	Spin injection and detection in lanthanum- and niobium-doped SrTiO <sub>3</sub> using the Hanle technique. Nature Communications, 2013, 4, 2134.	5.8	46
93	Structure and optical band gaps of (Ba,Sr)SnO <sub>3</sub> films grown by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	45
94	Quantification of trap densities at dielectric/III-V semiconductor interfaces. Applied Physics Letters, 2010, 97, .	1.5	44
95	Electric field-tunable Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> films with high figures of merit grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	1.5	44
96	Microstructure and Dielectric Properties of Textured SrTiO <sub>3</sub> Thin Films. Journal of the American Ceramic Society, 2005, 88, 789-801.	1.9	43
97	Ferroelectric enhancement of superconductivity in compressively strained SrTiO <sub>3</sub> thin films. Physical Review Materials, 2019, 3, .	1.9	43
98	ZrO <sub>2</sub> gate dielectrics produced by ultraviolet ozone oxidation for GaN and AlGaN/GaN transistors. Journal of Vacuum Science & Technology B, 2006, 24, 575.	1.3	42
99	Influence of orientation on the contrast of high-angle annular dark-field images of silicon. Physical Review B, 2007, 76, .	1.1	42
100	Effects of hydrogen anneals on oxygen deficient SrTiO <sub>3-x</sub> single crystals. Applied Physics Letters, 2008, 93, .	1.5	42
101	Metal-oxide-semiconductor capacitors with ZrO <sub>2</sub> dielectrics grown on In <sub>0.53</sub> Ga <sub>0.47</sub> As by chemical beam deposition. Applied Physics Letters, 2009, 95, 062908.	1.5	42
102	Two-dimensional Dirac fermions in thin films of Cd <sub>3</sub> As <sub>2</sub> . Applied Physics Letters, 2014, 105, 062102.	1.1	42
103	Accommodation of nonstoichiometry in (100) fiber-textured (Ba <sub>x</sub> Sr <sub>1-x</sub> )Ti <sub>1+y</sub> O <sub>3+z</sub> thin films grown by chemical vapor deposition. Applied Physics Letters, 1999, 74, 2432-2434.	1.5	41
104	dc electric field tunable bulk acoustic wave solidly mounted resonator using SrTiO <sub>3</sub> . Applied Physics Letters, 2007, 91, .	1.5	41
105	Ferroelectric transition in compressively strained SrTiO <sub>3</sub> thin films. Applied Physics Letters, 2015, 107, .	1.5	41
106	Composition control and dielectric properties of bismuth zinc niobate thin films synthesized by radio-frequency magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1745-1751.	0.9	40
107	Quantum confinement in oxide quantum wells. MRS Bulletin, 2013, 38, 1032-1039.	1.7	40
108	High performance raised source/drain InAs/In <sub>0.53</sub> Ga <sub>0.47</sub> As channel metal-oxide-semiconductor field-effect-transistors with reduced leakage using a vertical spacer. Applied Physics Letters, 2013, 103, .	1.5	40

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109	Surface reconstructions in molecular beam epitaxy of SrTiO <sub>3</sub> . Applied Physics Letters, 2014, 105, .	1.5	40
110	Order-Disorder Ferroelectric Transition of Strained $\text{SrTiO}_3$ . Physical Review Letters, 2020, 125, 087601.	2.9	40
111	Probing the metal-insulator transition of NdNiO <sub>3</sub> by electrostatic doping. Applied Physics Letters, 2011, 99, .	1.5	39
112	Suppression of Near-Fermi Level Electronic States at the Interface in a $\text{LaNiO}_3$ . Physical Review Letters, 2011, 107, 116402.	2.9	39
113	Growth and properties of GdTiO <sub>3</sub> films prepared by hybrid molecular beam epitaxy. Journal of Crystal Growth, 2012, 355, 166-170.	0.7	39
114	Conduction band edge effective mass of La-doped BaSnO <sub>3</sub> . Applied Physics Letters, 2016, 108, .	1.5	39
115	Novel Metal-Insulator Transition at the $\text{SmTiO}_3$ Interface. Physical Review Letters, 2017, 118, 236803.	2.9	39
116	The reaction between a TiNi shape memory thin film and silicon. Journal of Materials Research, 1997, 12, 1734-1740.	1.2	38
117	Extended defects in epitaxial Sc <sub>2</sub> O <sub>3</sub> films grown on (111) Si. Applied Physics Letters, 2005, 86, 051901.	1.5	38
118	Stoichiometry optimization of homoepitaxial oxide thin films using x-ray diffraction. Applied Physics Letters, 2009, 95, .	1.5	38
119	Modulation of over $10^{14}$ electrons in SrTiO <sub>3</sub> /GdTiO <sub>3</sub> heterostructures. Applied Physics Letters, 2014, 104, .	1.5	38
120	Correlation between metal-insulator transitions and structural distortions in high-electron-density SrTiO <sub>3</sub> quantum wells. Physical Review B, 2014, 89, .	1.1	38
121	High-temperature phase stability of hafnium aluminate films for alternative gate dielectrics. Journal of Applied Physics, 2004, 95, 3772-3777.	1.1	37
122	Scanning transmission electron microscopy of gate stacks with HfO <sub>2</sub> dielectrics and TiN electrodes. Applied Physics Letters, 2005, 87, 121909.	1.5	37
123	Ge <sub>1-x</sub> Mn <sub>x</sub> Clusters: Central Structural and Magnetic Building Blocks of Nanoscale Wire-Like Self-Assembly in a Magnetic Semiconductor. Nano Letters, 2009, 9, 3743-3748.	4.5	37
124	Tailoring resistive switching in Pt/SrTiO <sub>3</sub> junctions by stoichiometry control. Scientific Reports, 2015, 5, 11079.	1.6	37
125	Domain configurations in ferroelectric PbTiO <sub>3</sub> thin films: The influence of substrate and film thickness. Solid State Ionics, 1995, 75, 43-48.	1.3	36
126	Atomic Layer Deposition of Hafnium Oxide on Ge and GaAs Substrates: Precursors and Surface Preparation. Journal of the Electrochemical Society, 2008, 155, H937.	1.3	35



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127	Effect of postdeposition anneals on the Fermi level response of HfO <sub>2</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As gate stacks. Journal of Applied Physics, 2010, 108, .	1.1	35
128	Insulating state of ultrathin epitaxial LaNiO <sub>3</sub> thin films detected by hard x-ray photoemission. Physical Review B, 2011, 84, .	1.1	35
129	Influence of gate metallization processes on the electrical characteristics of high-k/In <sub>0.53</sub> Ga <sub>0.47</sub> As interfaces. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	34
130	Possible signatures of mixed-parity superconductivity in doped polar SrTiO <sub>3</sub> films. Physical Review B, 2020, 101, .	1.1	34
131	Oxygen vacancy ordering in epitaxial La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3</sub> thin films on (001) LaAlO <sub>3</sub> . Journal of Applied Physics, 2001, 90, 3319-3324.	1.1	33
132	Determining ferroelectric polarity at the nanoscale. Applied Physics Letters, 2011, 98, .	1.5	33
133	Charged Defect Quantification in PtAl <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As InP MOS Capacitors. Journal of the Electrochemical Society, 2011, 158, G103.	1.3	33
134	Quantum oscillations from a two-dimensional electron gas at a Mott/band insulator interface. Applied Physics Letters, 2012, 101, .	1.5	33
135	Temperature-dependence of the Hall coefficient of NdNiO <sub>3</sub> thin films. Applied Physics Letters, 2013, 103, 182105.	1.5	33
136	Key role of lattice symmetry in the metal-insulator transition of NdNiO <sub>3</sub> films. Scientific Reports, 2016, 6, 23652.	1.6	33
137	Probing the Metal-Insulator Transition in BaTiO <sub>3</sub> Electrostatic Doping. Physical Review Letters, 2016, 117, 037602.	2.9	33
138	BaTiO <sub>3</sub> /SrTiO <sub>3</sub> heterostructures for ferroelectric field effect transistors. Applied Physics Letters, 2017, 110, .	1.5	33
139	Design of Transistors Using High-Permittivity Materials. IEEE Transactions on Electron Devices, 2019, 66, 896-900.	1.6	33
140	Chemical, Physical, and Electrical Characterizations of Oxygen Plasma Assisted Chemical Vapor Deposited Yttrium Oxide on Silicon. Journal of the Electrochemical Society, 2003, 150, F102.	1.3	32
141	Growth modes in metal-organic molecular beam epitaxy of TiO <sub>2</sub> on r-plane sapphire. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 230-233.	0.9	32
142	Carrier density independent scattering rate in SrTiO <sub>3</sub> -based electron liquids. Scientific Reports, 2016, 6, 20865.	1.6	32
143	Polar Nanodomains in a Ferroelectric Superconductor. Nano Letters, 2020, 20, 6542-6547.	4.5	32
144	Electron energy-loss spectroscopy study of thin film hafnium aluminates for novel gate dielectrics. Journal of Microscopy, 2003, 210, 74-79.	0.8	31

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145	Anisotropic magnetoresistance in the itinerant antiferromagnetic $\text{EuTi}_3\text{O}_7$ . Physical Review B, 2019, 99, .	1.1	31
146	Scanning transmission electron microscopy investigations of interfacial layers in $\text{HfO}_2$ gate stacks. Journal of Applied Physics, 2006, 100, 024103.	1.1	30
147	Microstructure and dielectric properties of pyrochlore $\text{Bi}_2\text{Ti}_2\text{O}_7$ thin films. Journal of Applied Physics, 2007, 102, .	1.1	30
148	Thermal diffuse scattering in transmission electron microscopy. Ultramicroscopy, 2011, 111, 1670-1680.	0.8	30
149	Gaps and pseudogaps in perovskite rare earth nickelates. APL Materials, 2015, 3, 062503.	2.2	30
150	Low-loss tunable capacitors fabricated directly on gold bottom electrodes. Applied Physics Letters, 2006, 88, 112905.	1.5	29
151	Two-dimensional electron gas in a modulation-doped $\text{SrTiO}_3/\text{Sr}(\text{Ti}, \text{Zr})\text{O}_3$ heterostructure. Applied Physics Letters, 2013, 103, 082120.	1.5	29
152	Variable-angle high-angle annular dark-field imaging: application to three-dimensional dopant atom profiling. Scientific Reports, 2015, 5, 12419.	1.6	29
153	$(\text{Ba}, \text{Sr})\text{TiO}_3$ tunable capacitors with RF commutation quality factors exceeding 6000. Applied Physics Letters, 2016, 109, 112902.	1.5	29
154	Energetic, spatial, and momentum character of the electronic structure at a buried interface: The two-dimensional electron gas between two metal oxides. Physical Review B, 2016, 93, .	1.1	29
155	Scanning transmission electron microscopy of $\text{ErAs}$ nanoparticles embedded in epitaxial $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ layers. Applied Physics Letters, 2005, 86, 111912.	1.5	28
156	Distributed phase shifter with pyrochlore bismuth zinc niobate thin films. IEEE Microwave and Wireless Components Letters, 2006, 16, 264-266.	2.0	28
157	Influence of trimethylaluminum on the growth and properties of $\text{HfO}_2/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ interfaces. Applied Physics Letters, 2011, 98, 052911.	1.5	28
158	Reactions of $\text{Y}_2\text{O}_3$ films with (001) Si substrates and with polycrystalline Si capping layers. Applied Physics Letters, 2002, 81, 712-714.	1.5	27
159	Widely Tunable Optical and Thermal Properties of Dirac Semimetal $\text{Cd}_3\text{As}_2$ . Advanced Optical Materials, 2020, 8, 1901192.	3.6	27
160	Electron energy-loss spectroscopy analysis of interface structure of yttrium oxide gate dielectrics on silicon. Applied Physics Letters, 2002, 81, 676-678.	1.5	26
161	Thermal response of MOCVD hafnium silicate. Microelectronic Engineering, 2003, 69, 182-189.	1.1	26
162	Characterization of advanced gate stacks for Si CMOS by electron energy-loss spectroscopy in scanning transmission electron microscopy. Journal of Electron Spectroscopy and Related Phenomena, 2005, 143, 149-158.	0.8	26

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163	Analysis of carbon in SrTiO <sub>3</sub> grown by hybrid molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1365-1368.	0.9	26
164	The electrochemical impact on electrostatic modulation of the metal-insulator transition in nickelates. Applied Physics Letters, 2015, 106, .	1.5	26
165	Direct Observation of Sr Vacancies in SrTiO <sub>3</sub> . Quantitative Scanning Transmission Electron Microscopy. Physical Review X, 2016, 6, .	1.8	26
166	Electric field effect near the metal-insulator transition of a two-dimensional electron system in SrTiO <sub>3</sub> . Applied Physics Letters, 2017, 110, .	1.5	26
167	Soft phonons and ultralow lattice thermal conductivity in the Dirac semimetal Cd <sub>3</sub> As <sub>2</sub> . Physical Review Research, 2019, 1, .	1.3	26
168	High-density Two-Dimensional Small Polaron Gas in a Delta-Doped Mott Insulator. Scientific Reports, 2013, 3, 3284.	1.6	25
169	Highly Scalable Raised Source/Drain InAs Quantum Well MOSFETs Exhibiting $\mu_{\text{ON}} = 482 - \mu_{\text{OFF}}$ at $V_{\text{DD}} = 100 - V_{\text{DD}}$ and $V_{\text{DD}} = 0.5 - V_{\text{DD}}$ . IEEE Electron Device Letters, 2017, 38, 1200-1202.	2.2	25
170	Viscous energy dissipation at high temperatures in silicon nitride. Acta Materialia, 1998, 46, 4711-4723.	3.8	24
171	Carrier density control of magnetism and Berry phases in doped EuTiO <sub>3</sub> . APL Materials, 2018, 6, .	2.2	24
172	The influence of Pt and SrTiO <sub>3</sub> interlayers on the microstructure of PbTiO <sub>3</sub> thin films deposited by laser ablation on (001) MgO. Journal of Materials Research, 1995, 10, 791-794.	1.2	23
173	Microstructure of epitaxial Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> thin films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2000, 87, 3526-3531.	1.1	23
174	Composition control of radio-frequency magnetron sputter-deposited La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3-<math>\delta</math></sub> thin films. Journal of Materials Research, 2003, 18, 188-194.	1.2	23
175	Atomic structure of (111) SrTiO <sub>3</sub> Pt interfaces. Applied Physics Letters, 2006, 88, 131914.	1.5	23
176	Al-doped HfO <sub>2</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As metal-oxide-semiconductor capacitors. Applied Physics Letters, 2011, 98, 142901.	1.5	23
177	Extremely scaled high-k/In <sub>0.53</sub> Ga <sub>0.47</sub> As gate stacks with low leakage and low interface trap densities. Journal of Applied Physics, 2014, 116, 124104.	1.1	23
178	High-quality III-V semiconductor MBE growth on Ge/Si virtual substrates for metal-oxide-semiconductor device fabrication. Journal of Crystal Growth, 2009, 311, 1962-1971.	0.7	22
179	Magnetism and local structure in low-dimensional Mott insulating GdTiO <sub>3</sub> . Physical Review B, 2013, 88, .	1.1	22
180	Separation of transport lifetimes in SrTiO <sub>3</sub> -based two-dimensional electron liquids. Physical Review B, 2015, 91, .	1.1	22

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